

IRFR430APbF IRFU430APbF

HEXFET® Power MOSFET

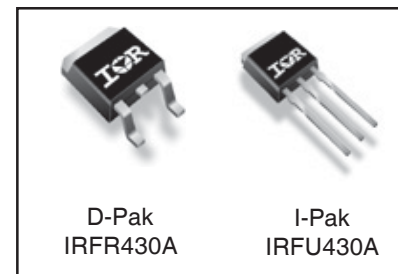
Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High speed power switching
- Lead-Free

Benefits

- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{oss} specified (See AN 1001)

V _{DSS}	R _{DS(on)} max	I _D
500V	1.7Ω	5.0A



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	5.0	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	3.2	
I _{DM}	Pulsed Drain Current ①	20	
P _D @ T _C = 25°C	Power Dissipation	110	W
	Linear Derating Factor	0.91	W/°C
V _{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	3.0	V/ns
T _J	Operating Junction and	-55 to + 150	
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	130	mJ
I _{AR}	Avalanche Current①	—	5.0	A
E _{AR}	Repetitive Avalanche Energy①	—	11	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.1	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.50	—	
R _{θJA}	Junction-to-Ambient	—	62	

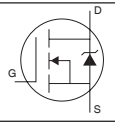
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.60	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	1.7	Ω	$V_{GS} = 10V, I_D = 3.0A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	2.3	—	—	S	$V_{DS} = 50V, I_D = 3.0A$
Q_g	Total Gate Charge	—	—	24	nC	$I_D = 5.0A$
Q_{gs}	Gate-to-Source Charge	—	—	6.5		$V_{DS} = 400V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	13		$V_{GS} = 10V$, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	8.7	—	ns	$V_{DD} = 250V$
t_r	Rise Time	—	27	—		$I_D = 5.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	17	—		$R_G = 15\Omega$
t_f	Fall Time	—	16	—		$R_D = 50\Omega$, See Fig. 10 ④
C_{iss}	Input Capacitance	—	490	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	75	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	4.5	—		$f = 1.0MHz$, See Fig. 5
C_{oss}	Output Capacitance	—	750	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	25	—		$V_{GS} = 0V, V_{DS} = 400V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	51	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$ ⑤

Diode Characteristics

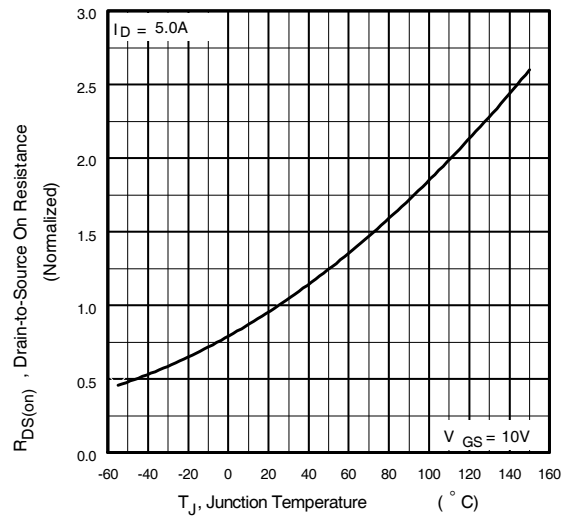
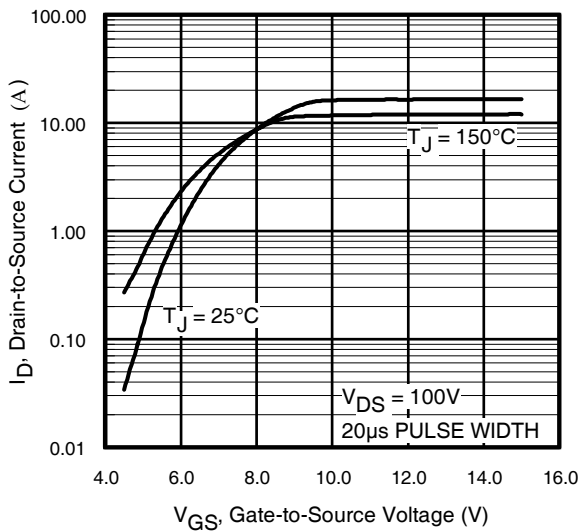
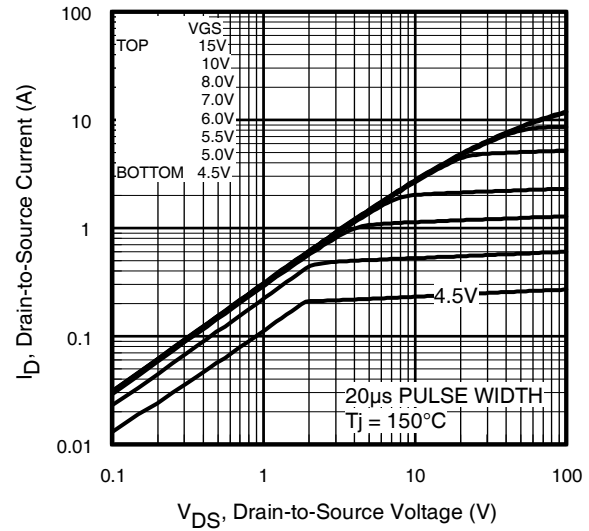
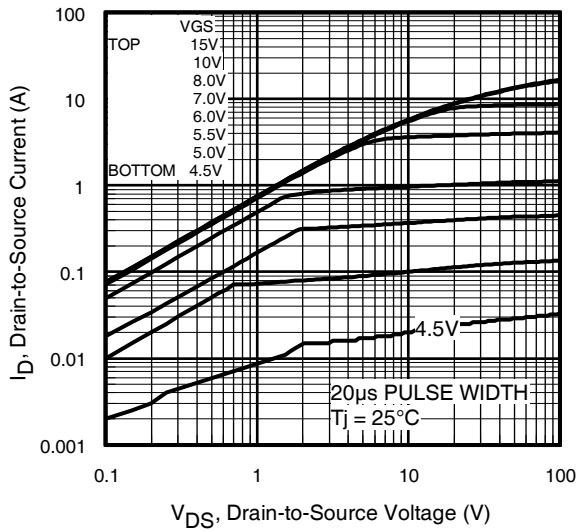
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	5.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	20		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 5.0A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	410	620	ns	$T_J = 25^\circ\text{C}, I_F = 5.0A$
Q_{rr}	Reverse Recovery Charge	—	1.4	2.1	μC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 11mH$
 $R_G = 25\Omega$, $I_{AS} = 5.0A$. (See Figure 12)
- ③ $I_{SD} \leq 5.0A$, $di/dt \leq 320A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 150^\circ\text{C}$.

- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

- ⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .



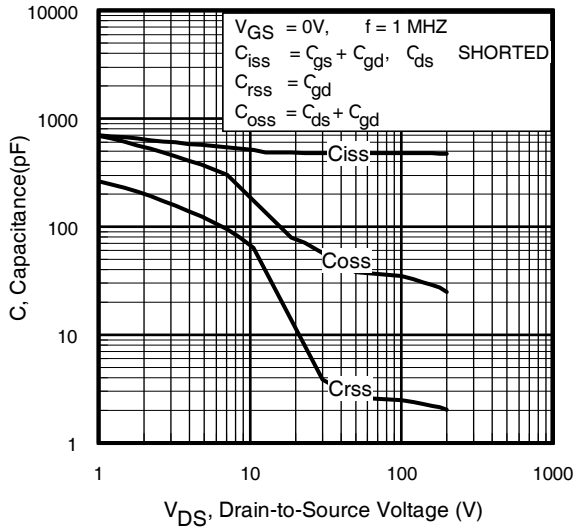


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

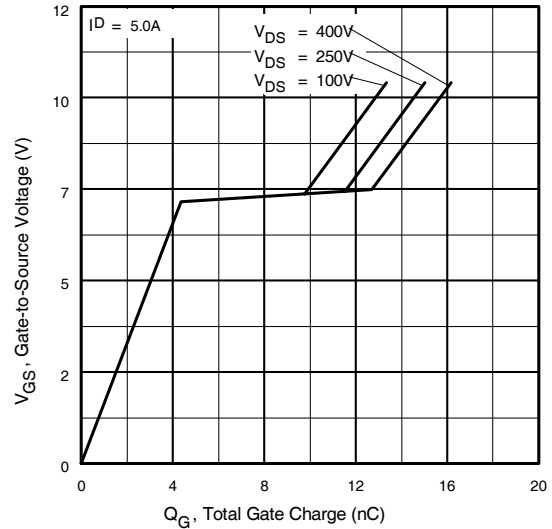


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

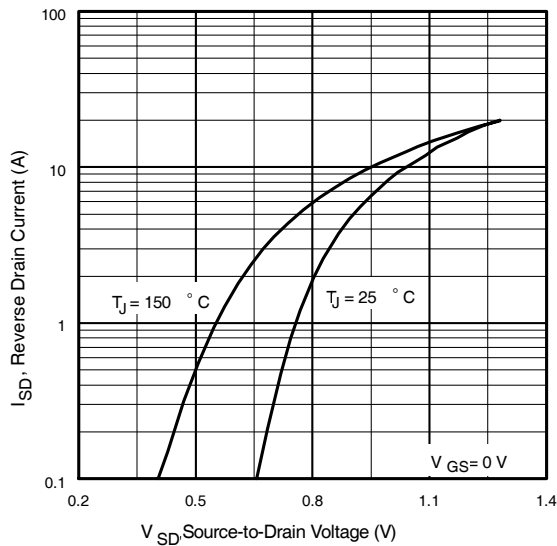


Fig 7. Typical Source-Drain Diode Forward Voltage

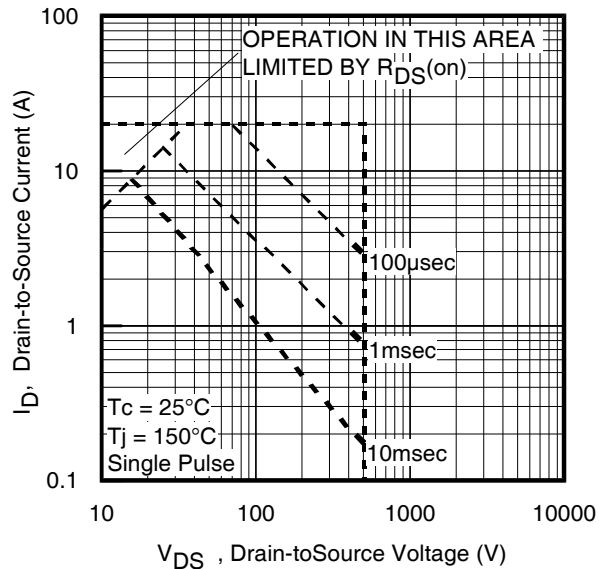


Fig 8. Maximum Safe Operating Area

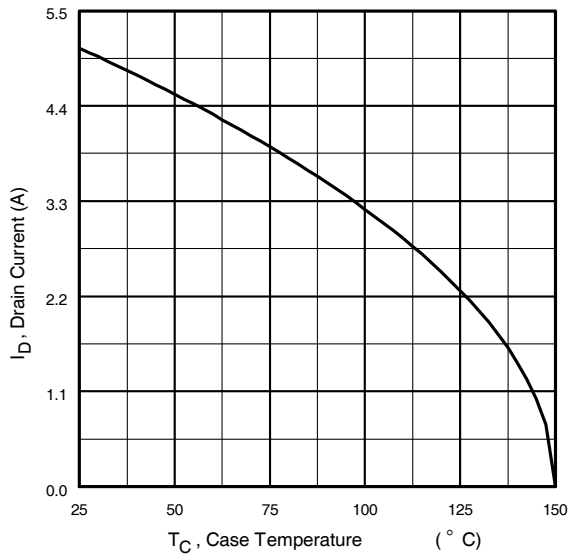


Fig 9. Maximum Drain Current Vs. Case Temperature

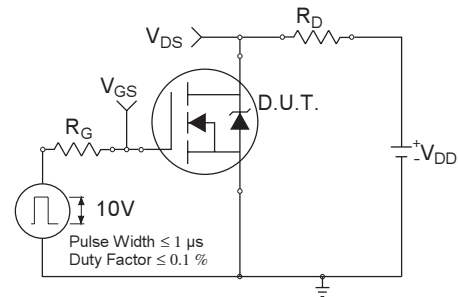


Fig 10a. Switching Time Test Circuit

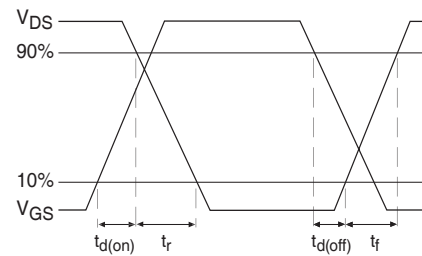


Fig 10b. Switching Time Waveforms

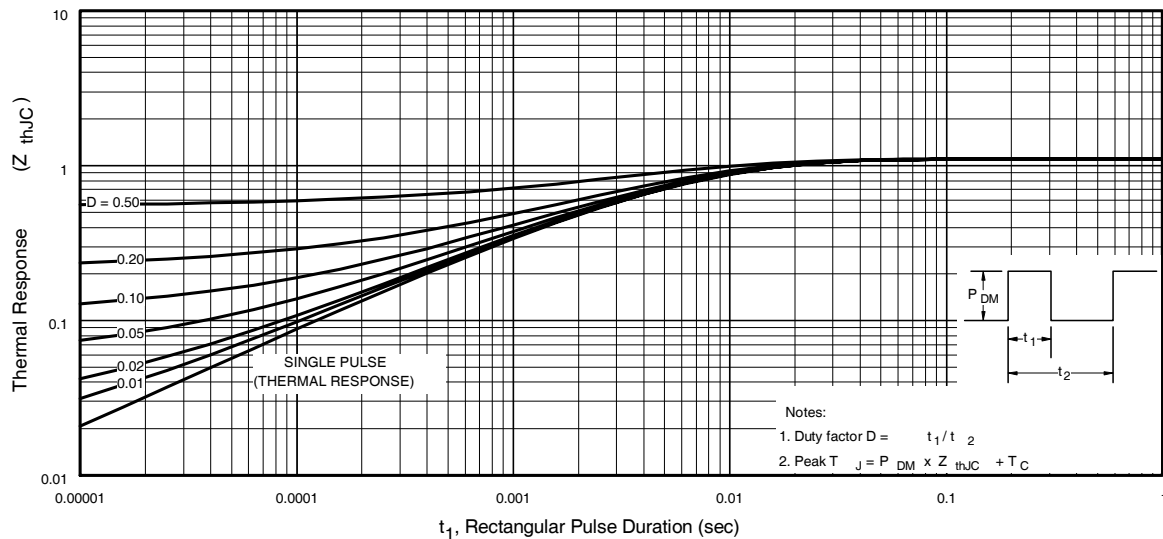


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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International
IR Rectifier

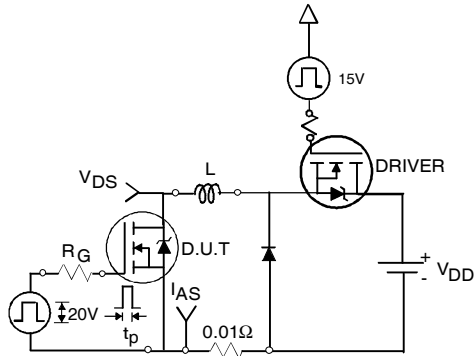


Fig 12a. Unclamped Inductive Test Circuit

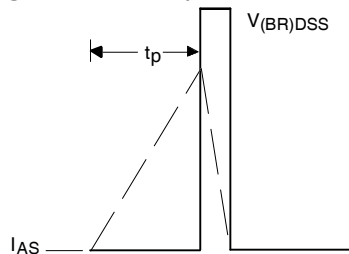


Fig 12b. Unclamped Inductive Waveforms

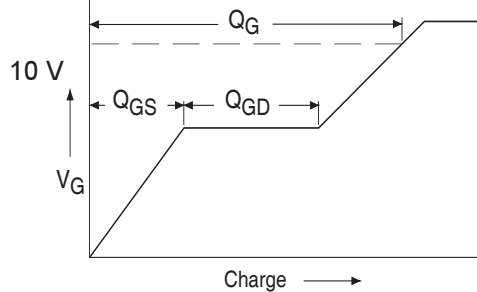


Fig 13a. Basic Gate Charge Waveform

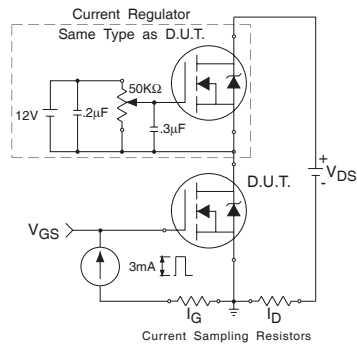


Fig 13b. Gate Charge Test Circuit

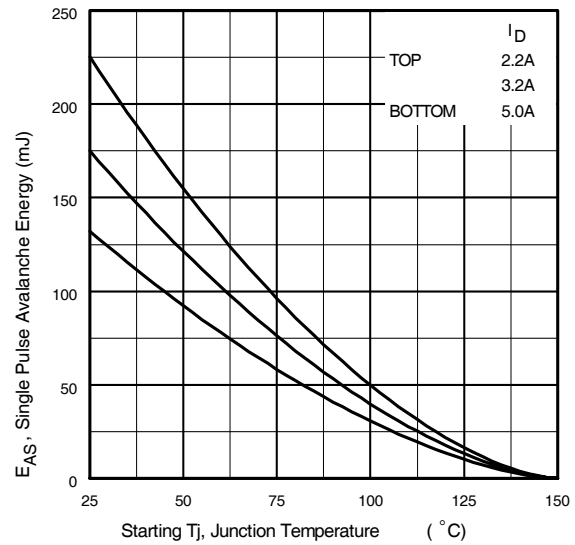


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

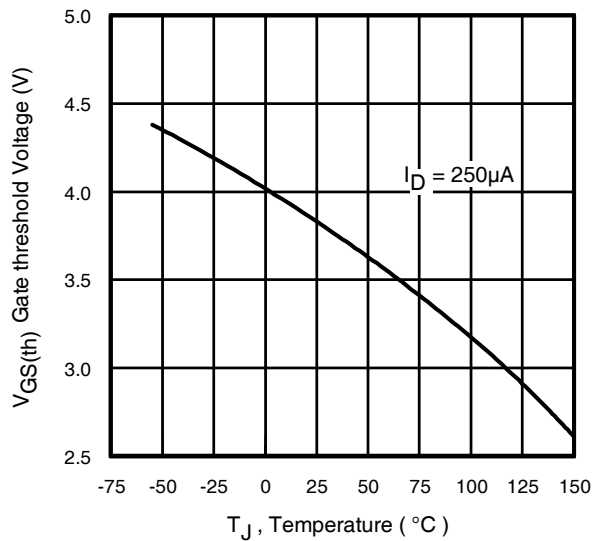
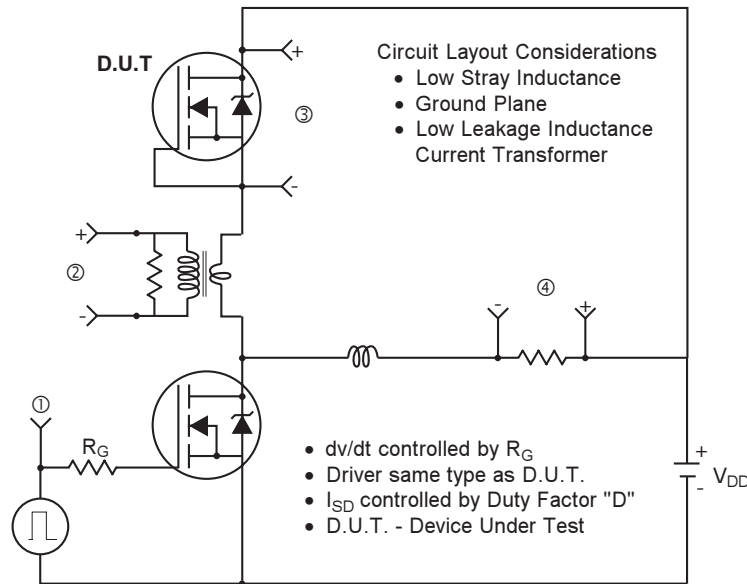


Fig 14. Threshold Voltage Vs. Temperature

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

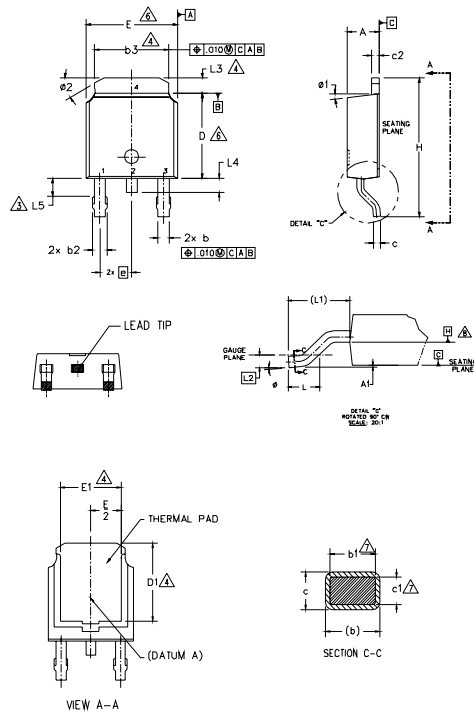
Fig 15. For N-Channel HEXFET® Power MOSFETs

IRFR/U430APbF

International
IR Rectifier

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- 3.- LEAD DIMENSION UNCONTROLLED IN L5.
- 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	—	0.13	—	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	—	.205	—	4
E	6.35	6.73	.250	.265	6
E1	4.32	—	.170	—	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	—	1.02	—	.040	
L5	1.14	1.52	.045	.060	3
ø	0*	10*	0*	10*	
ø1	0*	15*	0*	15*	
ø2	25*	35*	25*	35*	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

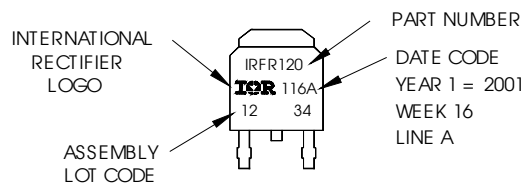
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

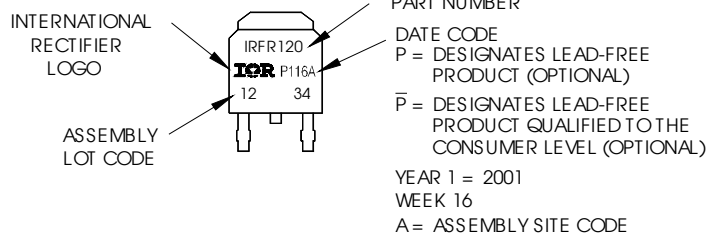
EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 2001
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

"P" in assembly line position indicates
"Lead-Free" qualification to the consumer-level

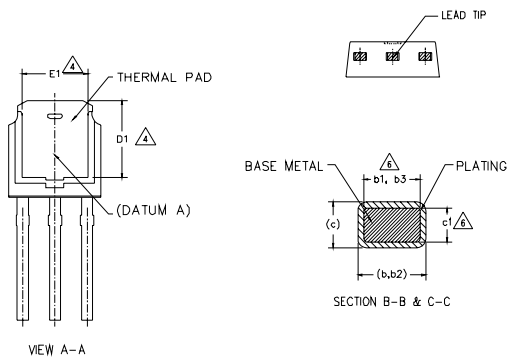
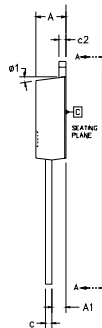
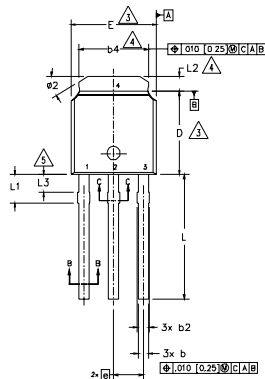


OR



I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. - DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994

2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].

3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.

4- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.

△5- LEAD DIMENSION UNCONTROLLED IN L3.

△6- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.

7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).

8.- CONTROLLING DIMENSION : INCHES.

S Y M B O L	DIMENSIONS				N O T E S
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	6
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	6
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	6
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	3
D1	5.21	—	.205	—	4
E	6.35	6.73	.250	.265	3
E1	4.32	—	.170	—	4
e	2.29 BSC		.090 BSC		
L	8.89	9.65	.350	.380	
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	4
L3	1.14	1.52	.045	.060	5
ø1	0" 15"		0"	15"	
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

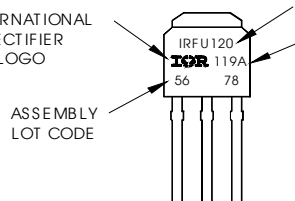
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 2001
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates Lead-Free"

OR

INTERNATIONAL
RECTIFIER
LOGO

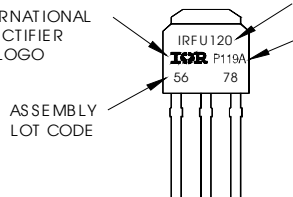


LOT CODE

PART NUMBER

DATE CODE
YEAR 1 = 2001
WEEK 19
LINE A

INTERNATIONAL
RECTIFIER
LOGO



ASSEMBLY
LOT CODE

PART NUMBER

DATE CODE
P = DESIGNATES LEAD-FREE
PRODUCT (OPTIONAL)

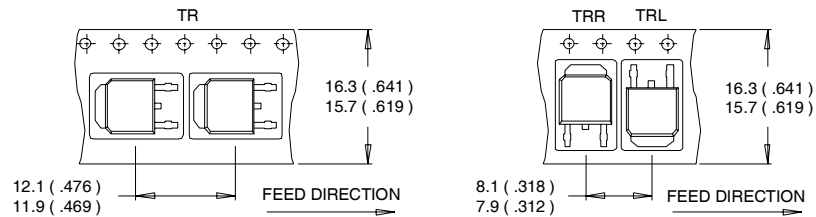
YEAR 1 = 2001
WEEK 19
A = ASSEMBLY SITE CODE

IRFR/U430APbF

International
IOR Rectifier

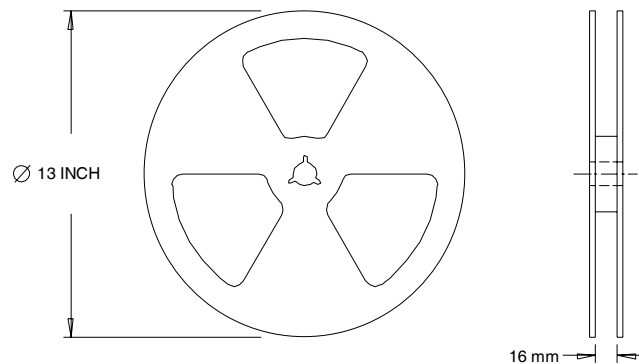
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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